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As usual, the Conference authors had a choice to submit their papers to the IEEE Conference Record of RADECS 2024 and/or to the IEEE Transactions on Nuclear Science Journal, each path of edition comprising its own Reviewing Committee.

As a result, a coherent Proceeding of the 2024 RADECS Conference results in the merging of two lists of papers which result from these paths.

51 papers resulted in Conference Record papers and 71 papers in IEEE Transactions on Nuclear Science papers. Both can be accessed in IEEEXplore, in the two different Sections.

Therefore, in the following we successively present two lists of papers ordered in two Sections, subsequently ordered by their place in the Conference Sessions.

Section I – Conference Papers

These papers were submitted to the Conference Review Committee and appear in the RADECS 2024 Conference Papers in IEEE Xplore (Conference Section, RADECS 2024).

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